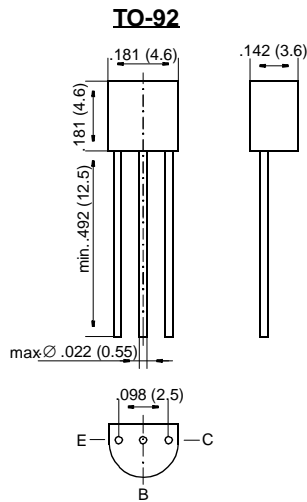


2N4126

Small Signal Transistors (PNP)



Dimensions in inches and (millimeters)

FEATURES

- ◆ PNP Silicon Epitaxial Transistor for switching and amplifier applications. Especially suitable for AF-driver and low-power output stages.
- ◆ As complementary type, the NPN transistor 2N4124 is recommended.



MECHANICAL DATA

Case: TO-92 Plastic Package

Weight: approx. 0.18 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Collector-Emitter Voltage	$-V_{CEO}$	25	V
Collector-Base Voltage	$-V_{CBO}$	25	V
Emitter-Base Voltage	$-V_{EBO}$	4	V
Collector Current	$-I_C$	200	mA
Peak Collector Current	$-I_{CM}$	800	mA
Base Current	$-I_B$	50	mA
Power Dissipation at $T_{amb} = 25\text{ °C}$	P_{tot}	625 ¹⁾	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	-65 to +150	°C

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

2N4126

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

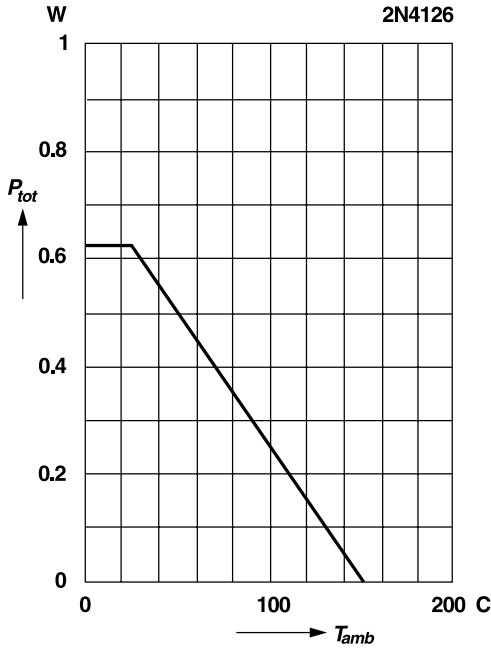
	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = -1$ V, $I_C = -2.0$ mA at $V_{CE} = -1$ V, $I_C = -50$ mA	h_{FE} h_{FE}	120 –	– 60	360 –	– –
Collector Cutoff Current at $V_{CB} = -20$ V	$-I_{CBO}$	–	–	50	nA
Emitter Cutoff Current at $V_{EB} = -3$ V	$-I_{EBO}$	–	–	50	nA
Collector Saturation Voltage at $I_C = -50$ mA, $I_B = -5$ mA	$-V_{CESAT}$	–	–	0.4	V
Base Saturation Voltage at $I_C = -50$ mA, $I_B = -5$ mA	$-V_{BESAT}$	–	–	0.95	V
Collector-Emitter Breakdown Voltage at $I_C = -1$ mA	$-V_{(BR)CEO}$	25	–	–	V
Collector-Base Breakdown Voltage at $I_C = -10$ μ A	$-V_{(BR)CBO}$	25	–	–	V
Emitter-Base Breakdown Voltage at $I_E = -10$ μ A	$-V_{(BR)EBO}$	4	–	–	V
Gain-Bandwidth Product at $V_{CE} = -5$ V, $I_C = -10$ mA, $f = 50$ MHz	f_T	–	200	–	MHz
Collector-Base Capacitance at $V_{CB} = -10$ V, $f = 1$ MHz	C_{CBO}	–	12	–	pF
Thermal Resistance Junction to Ambient Air	R_{thJA}	–	–	200 ¹⁾	K/W

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case.

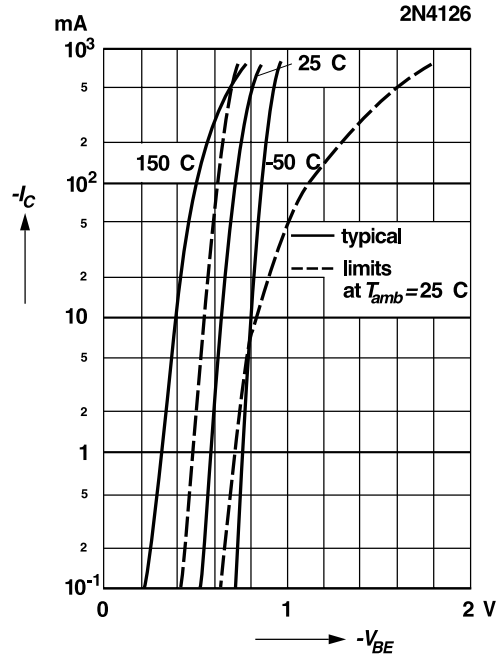
RATINGS AND CHARACTERISTIC CURVES 2N4126

Admissible power dissipation versus ambient temperature

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

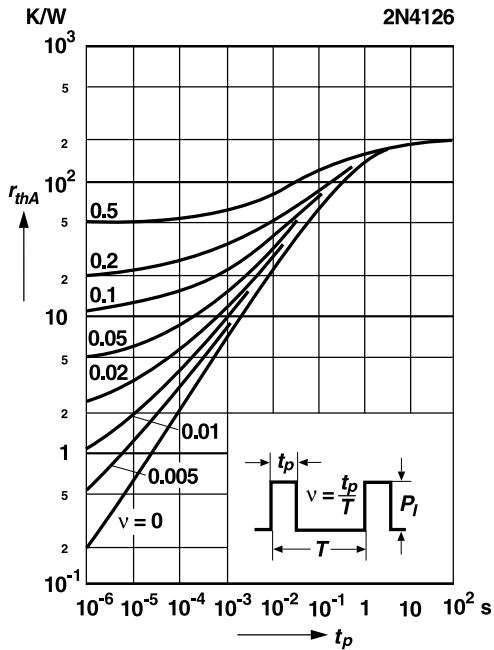


Collector current versus base-emitter voltage

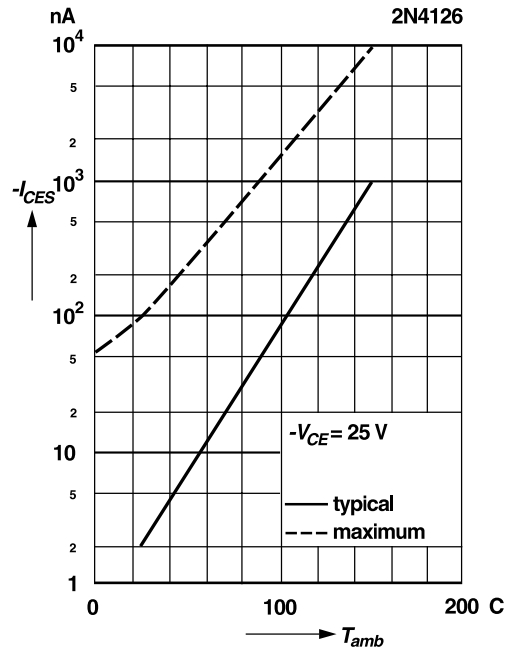


Pulse thermal resistance versus pulse duration

Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

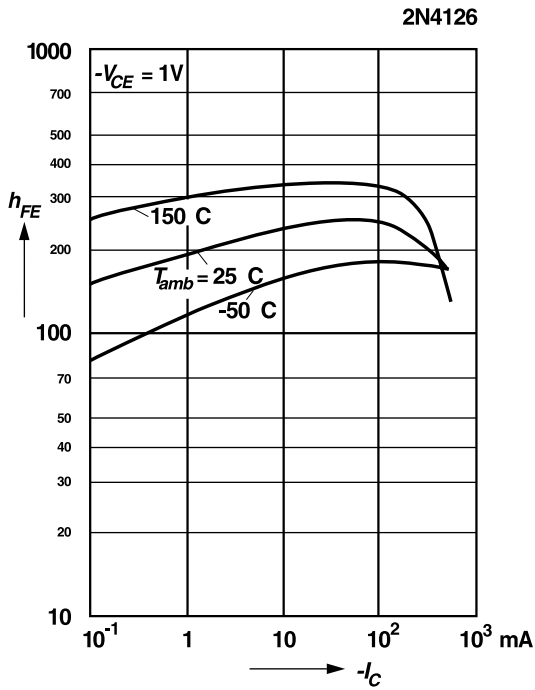


Collector-emitter cutoff current versus ambient temperature

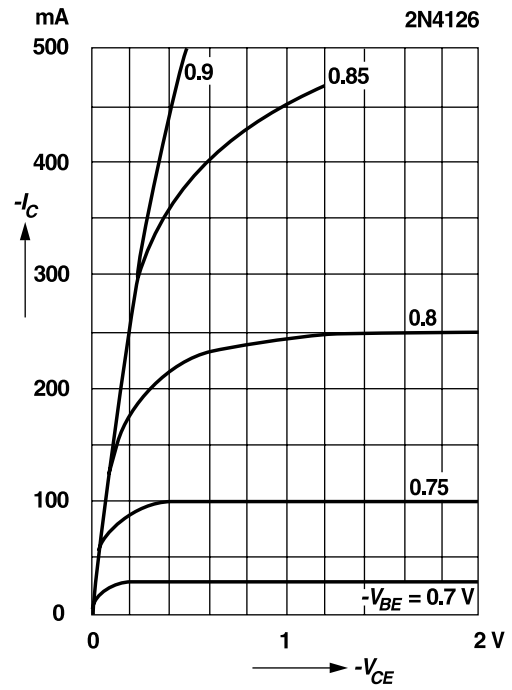


RATINGS AND CHARACTERISTIC CURVES 2N4126

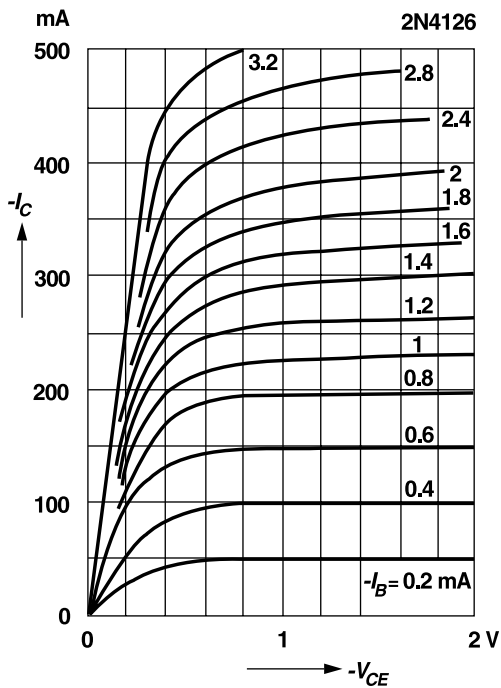
DC current gain
versus collector current



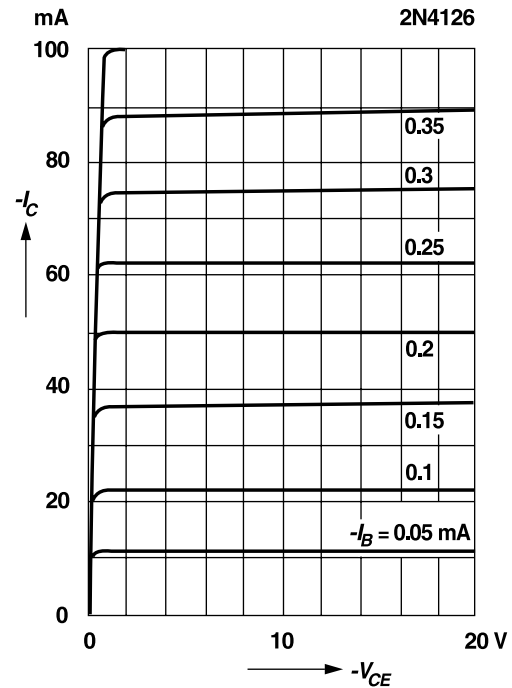
Common emitter
collector characteristics



Common emitter
collector characteristics

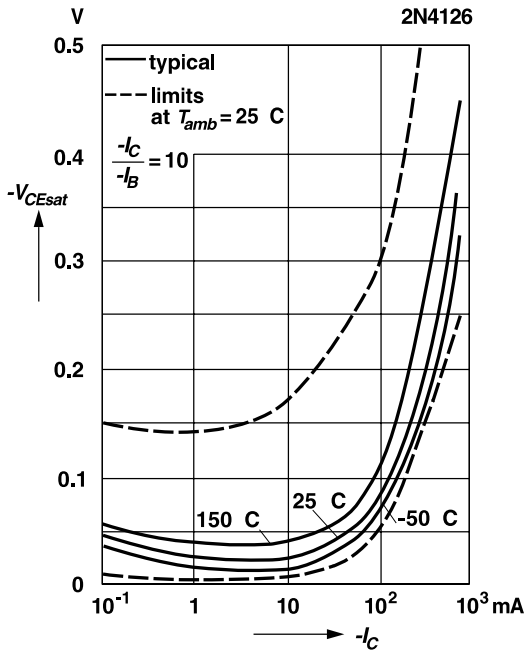


Common emitter
collector characteristics

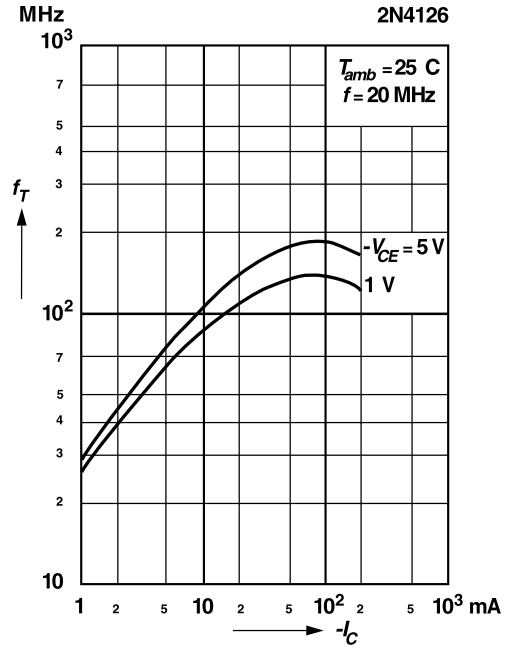


RATINGS AND CHARACTERISTIC CURVES 2N4126

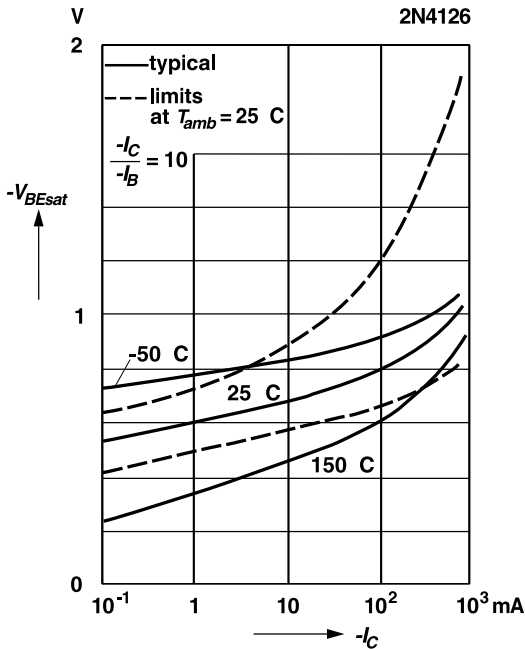
Collector saturation voltage
versus collector current



Gain-bandwidth product
versus collector current



Base saturation voltage
versus collector current



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Datasheets for electronics components.